

METHOD FOR PATTERN-FORMING BURIED OXIDE FILM THICKNESS FOR SIMOX (SILICON IMPLANTED OXIDE) PROCESS

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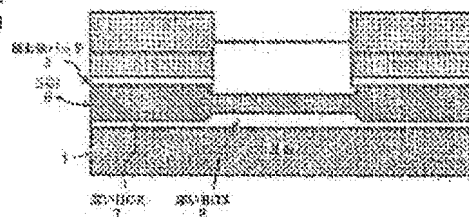
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Abstract of JP 2002009145 (A)

PROBLEM TO BE SOLVED: To provide a method for forming a pattern formation buried oxide film.

SOLUTION: The method for forming the pattern formation buried oxide film comprises a step of carrying out implantation into a substrate, a step of forming a mask at least on part of the substrate in order to control implantation diffusion, and a step of annealing the substrate and forming a buried oxide. The mask can be selectively pattern-formed. A thinner buried oxide can be formed in a region coated by the mask than in a region exposed to an annealing atmosphere directly.



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